

# MA2HD08

## Silicon epitaxial planar type

For high-frequency rectification

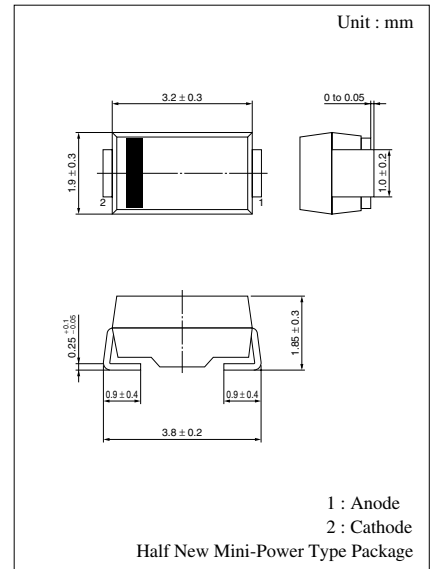
### ■ Features

- Small and thin Half New Mini-power package
- Allowing to rectify under ( $I_{F(AV)} = 1$  A) condition

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	30	V
Repetitive peak reverse voltage	$V_{RRM}$	30	V
Average forward current	$I_{F(AV)}$	1	A
Non-repetitive peak forward surge current*	$I_{FSM}$	25	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +125	$^\circ\text{C}$

Note) \* : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)



Marking Symbol: PP

### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 30$ V			13	mA
Forward voltage (DC)	$V_F$	$I_F = 1$ A			0.30	V
Terminal capacitance	$C_t$	$V_R = 10$ V, $f = 1$ MHz		50		pF
Reverse recovery time*	$t_{rr}$	$I_F = I_R = 100$ mA $I_{rr} = 0.1 \cdot I_R$ , $R_L = 100 \Omega$		15		ns

Note) 1. Rated input/output frequency: 20 MHz  
2. \* :  $t_{rr}$  measuring instrument

